

2SK2964

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance : R_{DSON} = 0.13 Ω (typ.)
- High forward transfer admittance : |Y_{fs}| = 2.5 S (typ.)
- Low leakage current : I_{DSS} = 100 μA (max) (V_{DS} = 30 V)
- Enhancement mode : V_{th} = 0.8~2.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V _{DSS}	30	V	
Drain-gate voltage (R _{GS} = 20 kΩ)	V _{DGR}	30	V	
Gate-source voltage	V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	2	A
	Pulse (Note 1)	I _{DP}	6	A
Drain power dissipation	P _D	0.5	W	
Drain power dissipation (Note 2)	P _D	1.5	W	
Single pulse avalanche energy (Note 3)	E _{AS}	56	mJ	
Avalanche current	I _{AR}	2	A	
Repetitive avalanche energy (Note 4)	E _{AR}	0.05	mJ	
Channel temperature	T _{ch}	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

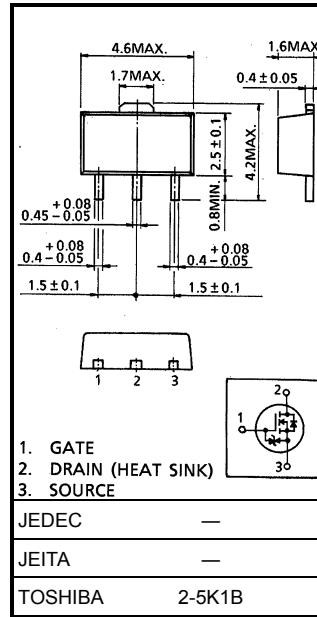
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th(ch-a)}	250	°C / W

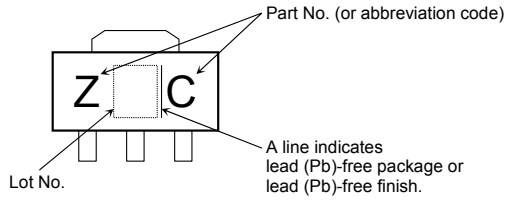
- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Mounted on a ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)
- Note 3: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 10 mH, R_G = 25 Ω, I_{AR} = 2 A
- Note 4: Repetitive rating: pulse width limited by maximum channel temperature
- This transistor is an electrostatic-sensitive device.
Please handle with caution.

Unit: mm



Weight: 0.05 g (typ.)

Marking

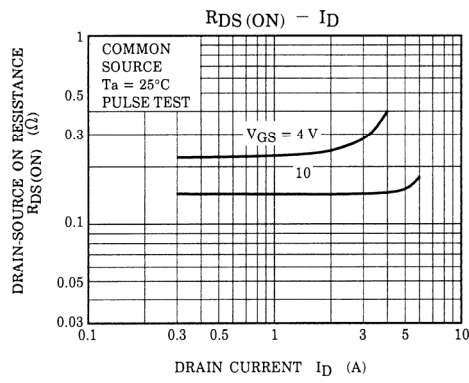
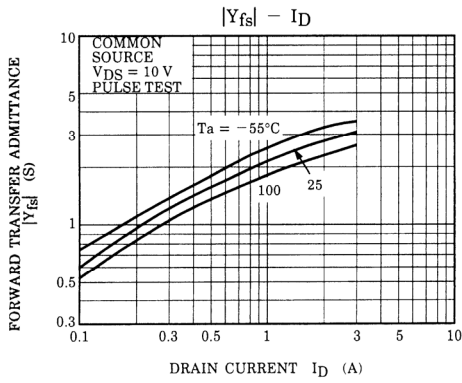
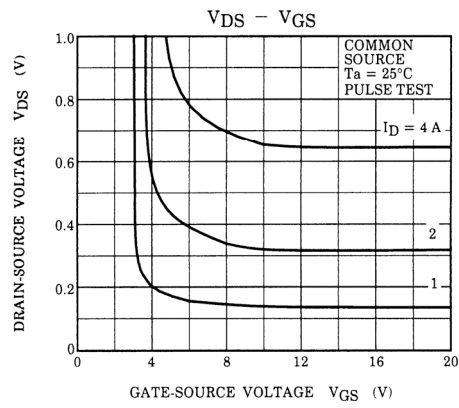
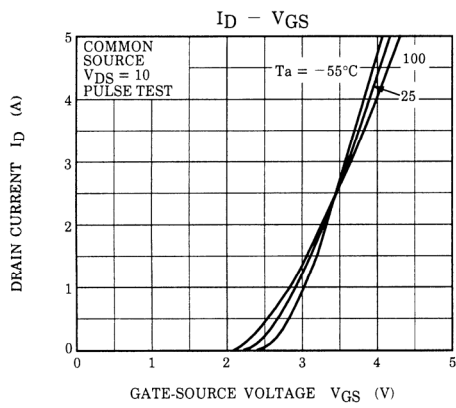
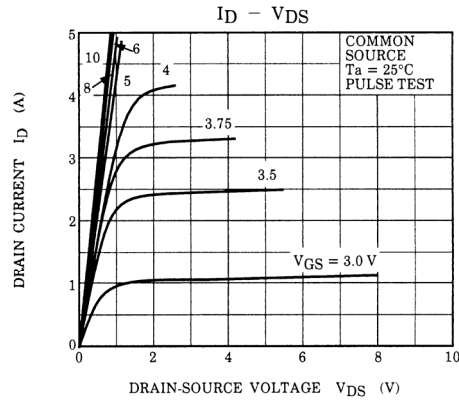
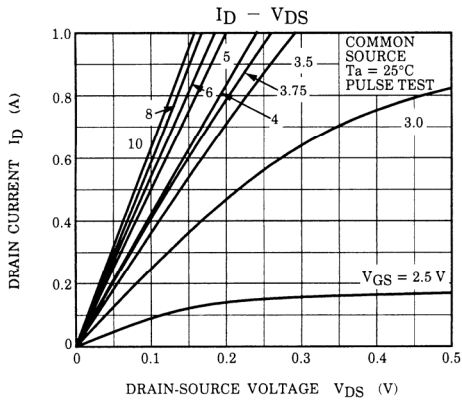


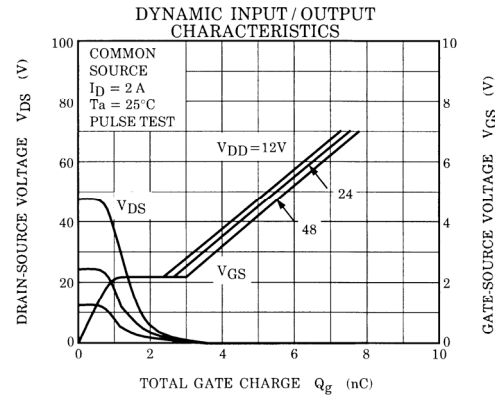
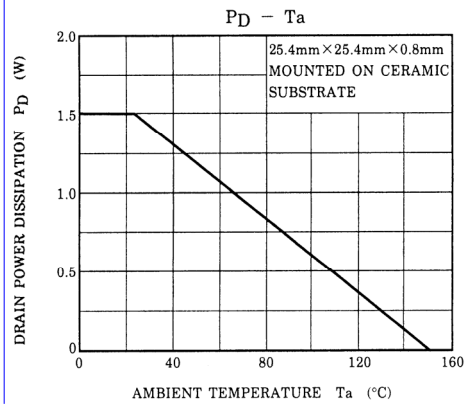
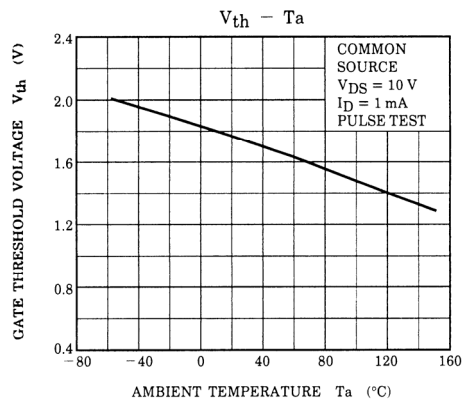
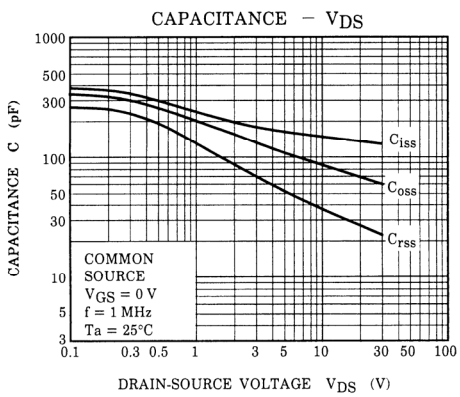
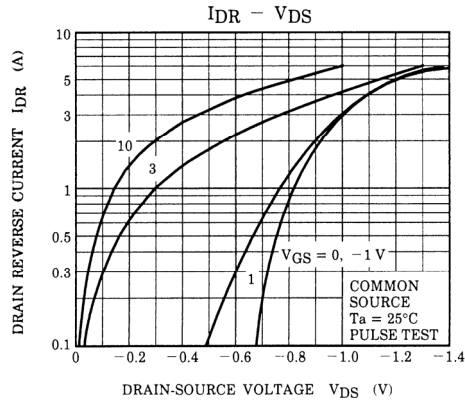
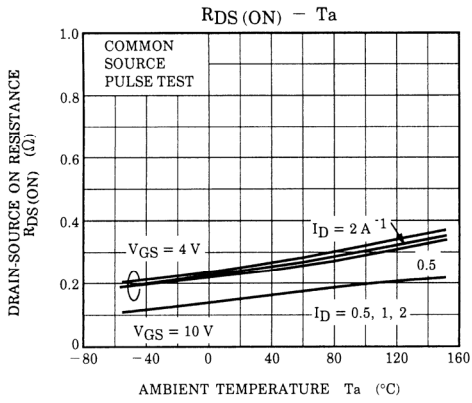
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	30	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.8	—	2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 1\text{ A}$	—	0.18	0.25	Ω
			$V_{GS} = 10\text{ V}, I_D = 1\text{ A}$	—	0.13	0.18	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 1\text{ A}$	1.2	2.5	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	140	—	pF
Reverse transfer capacitance		C_{rss}		—	30	—	
Output capacitance		C_{oss}		—	80	—	
Switching time	Rise time	t_r		—	10	—	ns
	Turn-on time	t_{on}		—	15	—	
	Fall time	t_f		—	85	—	
	Turn-off time	t_{off}		—	195	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 2\text{ A}$	—	5.8	—	nC
Gate-source charge		Q_{gs}		—	4.3	—	
Gate-drain ("miller") Charge		Q_{gd}		—	1.5	—	

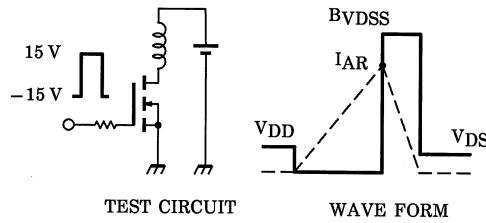
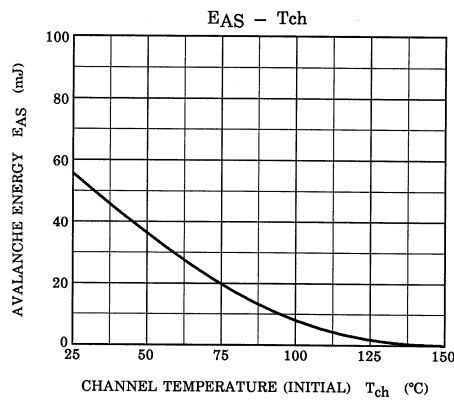
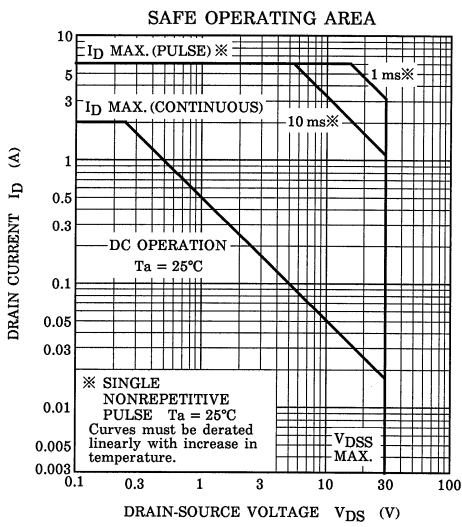
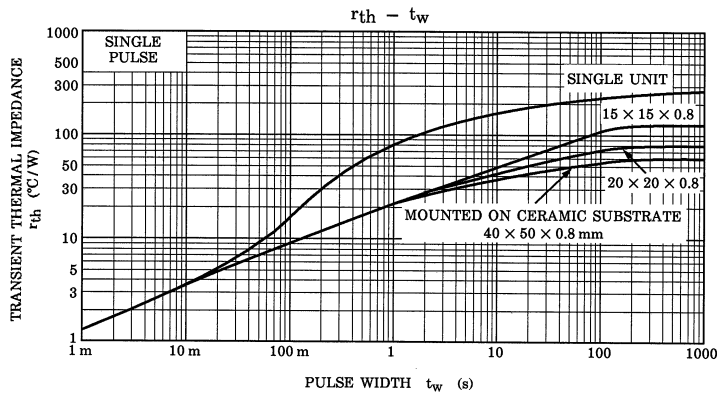
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	2	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	6	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 2\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = 2\text{ A}, V_{GS} = 0\text{ V}, dI_{DR} / dt = 50\text{ A} / \mu\text{s}$	—	50	—	ns
Reverse recovery charge	Q_{rr}		—	20	—	nC





コメント [H2]: Mounted on a ceramic substrate
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$R_G = 25 \Omega$
 $V_{DD} = 25 \text{ V}, L = 10 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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